



TO-92 Plastic-Encapsulate Transistors

BC327/ BC328 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

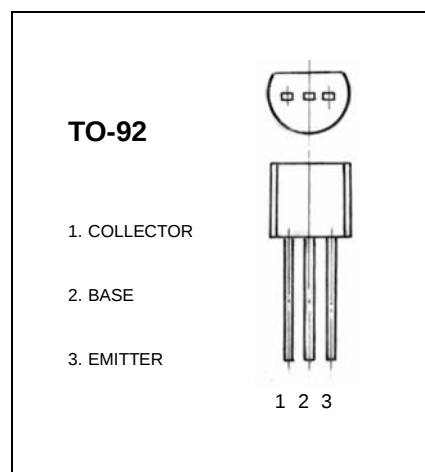
I_{CM} : -0.8 A

Collector-base voltage

V_{CBO} : BC327 -50 V
BC328 -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu A, I_E = 0$				
BC327			-50			V
BC328			-30			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10 mA, I_B = 0$				
BC327			-45			V
BC328			-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$			-0.1 -0.1	μA μA
Collector cut-off current	I_{CEO}	$V_{CE} = -40V, I_B = 0$ $V_{CE} = -20 V, I_B = 0$			-0.2 -0.2	μA μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		630	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -300mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 mA, I_B = -50 mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 mA, I_B = -50 mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	260			MHz

h_{FE} CLASSIFICATION

Classification	16	25	40
h_{FE1}	100-250	160-400	250-630
h_{FE2}	60-	100-	170-